

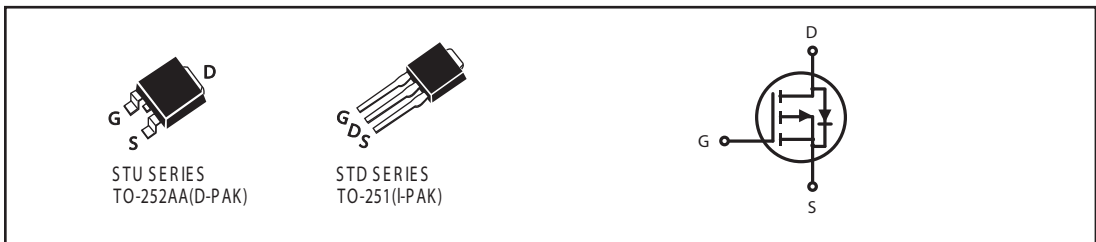


## P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (m $\Omega$ ) Max
-55V	-12A	110 @ V <sub>GS</sub> = -10V
		145 @ V <sub>GS</sub> = -4.5V

## FEATURES

- Super high dense cell design for low R<sub>DS(ON)</sub>.
- Rugged and reliable.
- TO-252 and TO-251 Package.

ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V <sub>spike</sub> <sup>d</sup>	60	V
Drain-Source Voltage	V <sub>DS</sub>	-55	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous <sup>a</sup> @ T <sub>a</sub>	I <sub>D</sub>	25°C	-12
		70°C	-10
-Pulsed <sup>b</sup>	I <sub>DM</sub>	-23	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	-15	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>a</sub> =25°C	50
		T <sub>a</sub> =70°C	35
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 175	°C

## THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R $\theta$ JC	3	°C/W
Thermal Resistance, Junction-to-Ambient	R $\theta$ JA	50	°C/W

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250uA	-55			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -44V, V <sub>GS</sub> = 0V			-1	uA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>ON CHARACTERISTICS<sup>b</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1.3	-1.8	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A		95	110	m-ohm
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6A		120	145	m-ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -10V	30			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -10A		12		S
<b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V f = 1.0MHz		770	885	pF
Output Capacitance	C <sub>OSS</sub>			80	94	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			55	65	pF
<b>SWITCHING CHARACTERISTICS<sup>c</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>D</sub> = -30V, I <sub>D</sub> = -1A, V <sub>GEN</sub> = -10V, R <sub>GEN</sub> = 6 ohm		12.3	14	ns
Rise Time	t <sub>r</sub>			8.8	10	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			51.5	60	ns
Fall Time	t <sub>f</sub>			23.1	26	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A, V <sub>GS</sub> = -10V		13.7	16	nC
		V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A, V <sub>GS</sub> = -4.5V		6.8	8	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> = -30V, I <sub>D</sub> = -5A, V <sub>GS</sub> = 10V		2.5	3	nC
Gate-Drain Charge	Q <sub>gd</sub>			2.8	3.3	nC

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## ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS<sup>b</sup></b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_s = -15A$		-1	-1.3	V

### Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.
- d. Guaranteed when external  $R_g = 6\text{ ohm}$  and  $t_f < t_{f\text{ max}}$

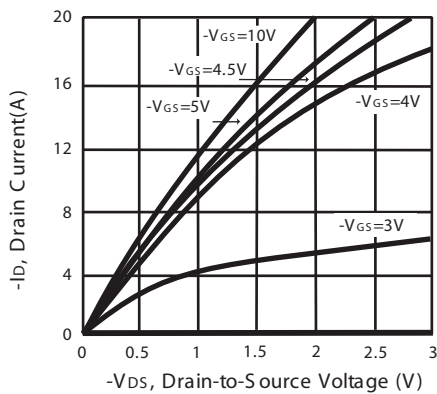


Figure 1. Output Characteristics

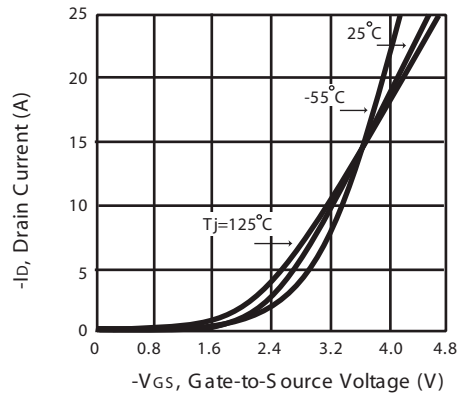


Figure 2. Transfer Characteristics

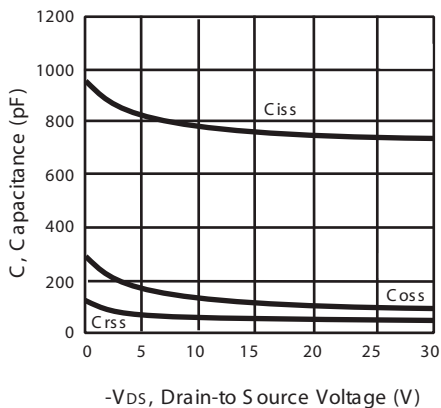


Figure 3. Capacitance

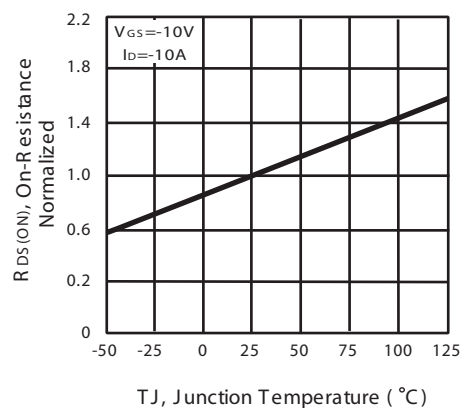


Figure 4. On-Resistance Variation with Temperature

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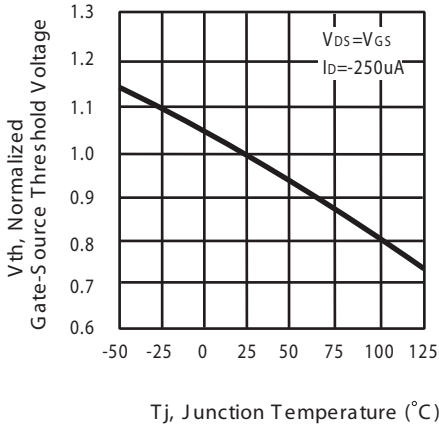


Figure 5. Gate Threshold Variation with Temperature

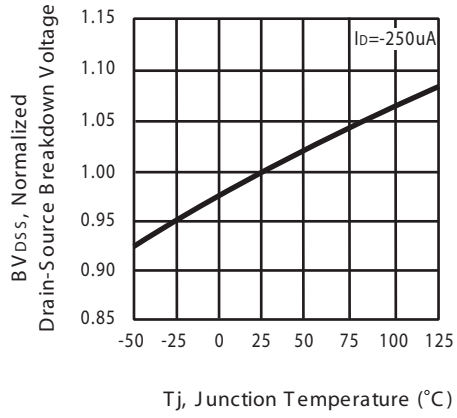


Figure 6. Breakdown Voltage Variation with Temperature

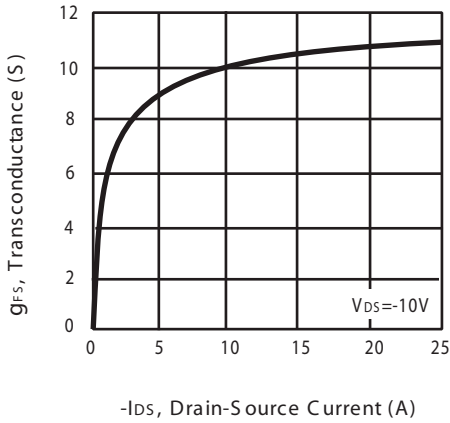


Figure 7. Transconductance Variation with Drain Current

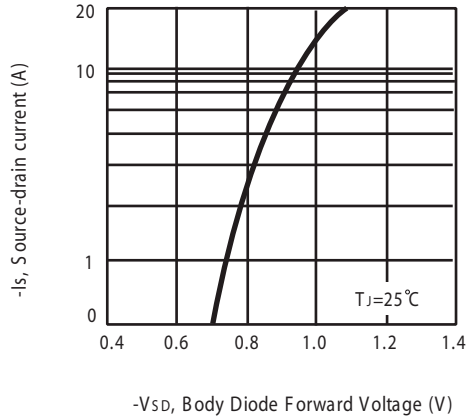


Figure 8. Body Diode Forward Voltage Variation with Source Current

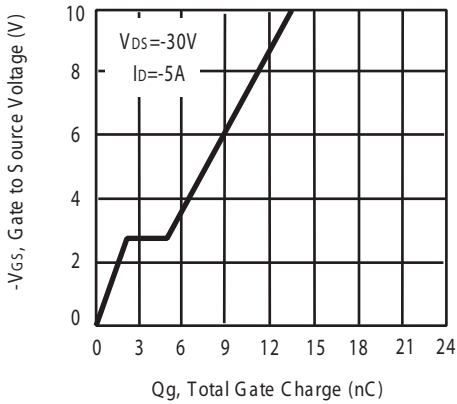


Figure 9. Gate Charge

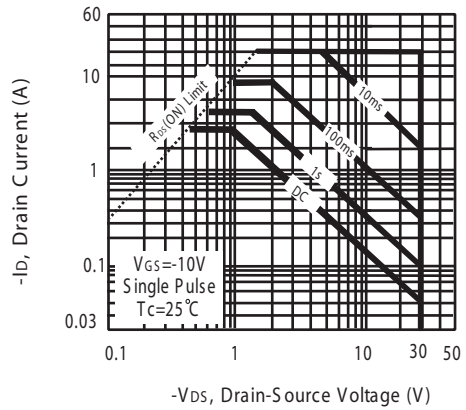


Figure 10. Maximum Safe Operating Area

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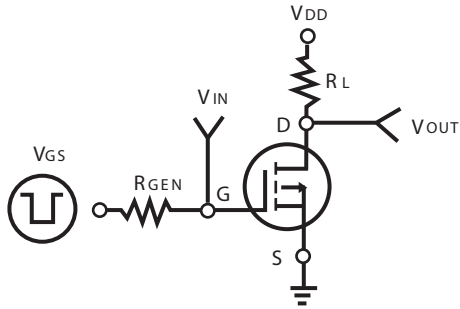


Figure 11. Switching Test Circuit

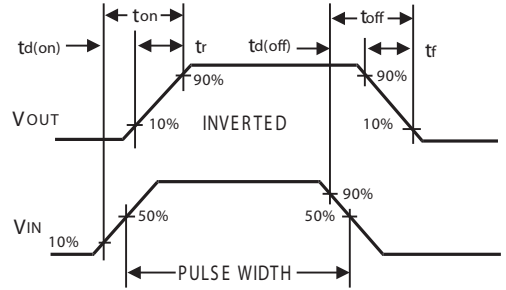
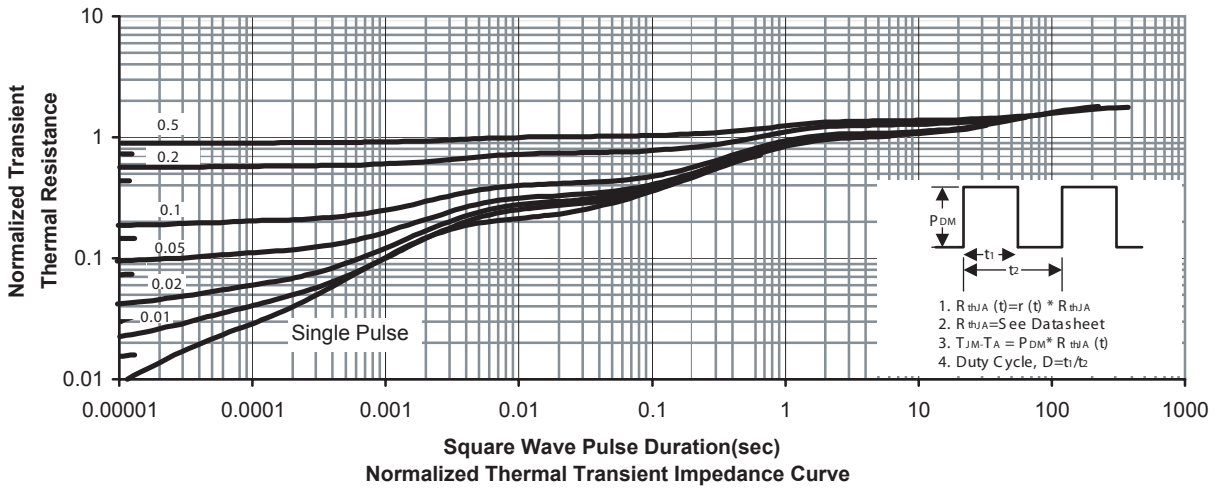


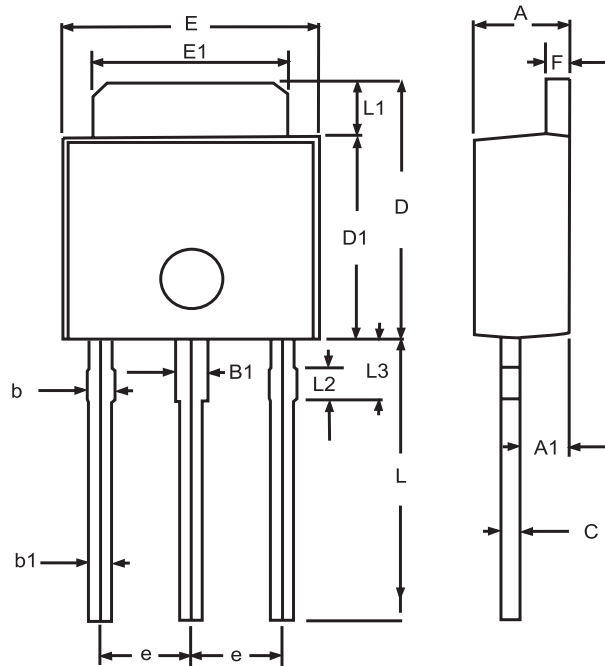
Figure 12. S switching Waveforms



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## PACKAGE OUTLINE DIMENSIONS

### TO-251

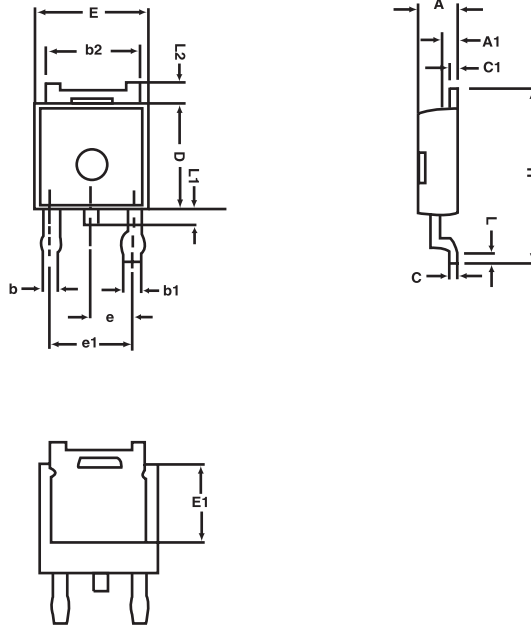


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.20	2.40	0.087	0.095
A1	1.100	1.300	0.043	0.051
B1	0.650	1.050	0.026	0.041
b	0.500	0.900	0.020	0.035
b1	0.400	0.800	0.016	0..32
C	0.400	0.600	0.016	0.024
D	6.700	7.300	0.264	0.287
D1	5.400	5.650	0.213	0.222
E	6.40	6.650	0.252	0.262
e	2.100	2.500	0.083	0.098
F	0.400	0.600	0.016	0.024
L	7.000	8.000	0.276	0.315
L1	1.300	1.700	0.051	0.067
L2	0.700	0.900	0.028	0.035
L3	1.400	1.800	0.055	0.071

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## PACKAGE OUTLINE DIMENSIONS

### TO-252



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.25	2.35	0.089	0.093
A1	0.95	1.05	0.037	0.041
b	0.77	0.85	0.030	0.033
b1	0.84	0.94	0.033	0.037
b2	5.30	5.45	0.209	0.215
C	0.49	0.53	0.019	0.021
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.252	0.260
E1	3.18	3.67	0.125	0.145
e	2.29	BSC	0.090	BSC
H	9.70	10.10	0.382	0.398
L	1.425	1.625	0.056	0.064
L1	0.650	0.850	0.026	0.033
L2	0.600	REF.	0.024	REF.

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## TO251 Tube/TO-252 Tape and Reel Data

### TO-251 Tube



### TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 0.3±	1.75 0.1±	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

### TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---